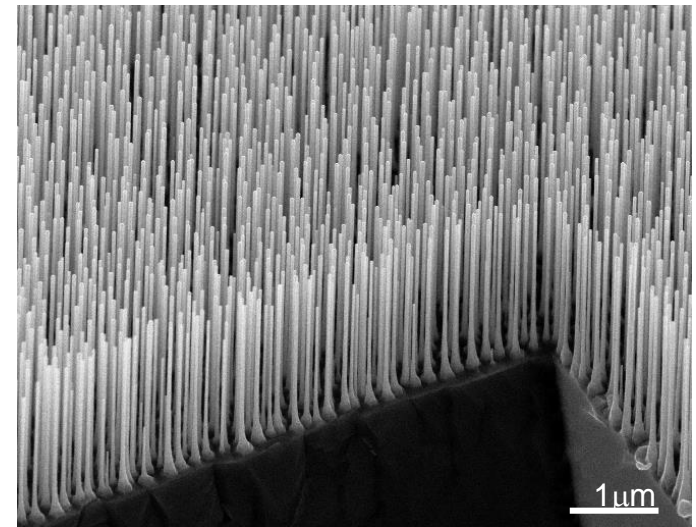


# Growth and characterization of semiconductor nanowires by Chemical Beam Epitaxy

The students will learn the working procedures of the Chemical Beam Epitaxy technique for the synthesis of nanowires and related nano-heterostructures of III-V semiconductor materials (InAs, InP, GaAs, InSb, GaSb, ecc.)

The grown structures will be characterized by means of microscopic and spectroscopic techniques (scanning electron microscopy and energy dispersive X-ray spectroscopy)



Contact person: Prof. Lucia Sorba (lucia.sorba@nano.cnr.it)